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PSMN3R9-60PS

N-channel 60 V, 3.9 mΩ standard level MOSFET in SOT78

1 February 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in SOT78 using TrenchMOS technology. Product design and manufacture has been optimized for use in battery operated power tools.

2. Features and benefits

- High efficiency due to low switching & conduction losses
- Robust construction for demanding applications
- Standard level gate

3. Applications

- Battery-powered tools
- Load switching
- Motor control
- Uninterruptible power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 1	[1]	-	-	130	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	-	263	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	2.94	3.9	mΩ
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 13 ; Fig. 14		-	103	-	nC
Q _{GD}	gate-drain charge			-	33	-	nC
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 130 A; V _{sup} ≤ 60 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{J(init)} = 25 °C; unclamped; Fig. 3		-	-	283	mJ

[1] Continuous current is limited by package.



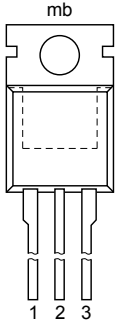
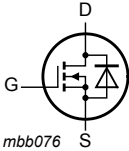
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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-220AB (SOT78)</p>	
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R9-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN3R9-60PS	PSMN3R9-60PS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^\circ\text{C}$; $T_j \leq 175\text{ }^\circ\text{C}$		-	60	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$T_{mb} = 25\text{ }^\circ\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 1	[1]	-	130	A
		$T_{mb} = 100\text{ }^\circ\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 1		-	127	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^\circ\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4		-	705	A

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Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 2		-	263	W
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ °C}$	[1]	-	130	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ °C}$		-	705	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 130\text{ A}$; $V_{sup} \leq 60\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; unclamped; Fig. 3		-	283	mJ

[1] Continuous current is limited by package.

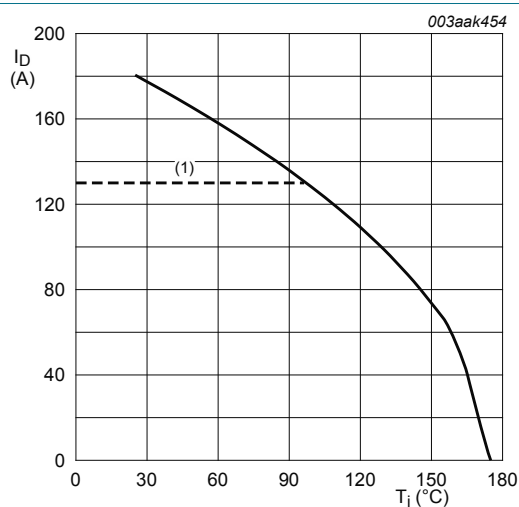


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10\text{ V}$$

(1) Capped at 130 A due to package.

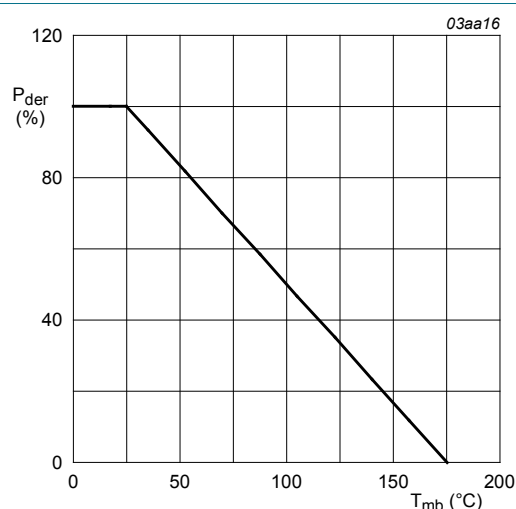


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ °C})}} \times 100\%$$

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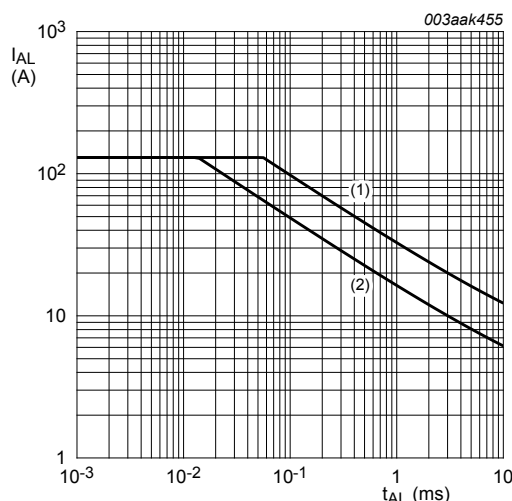


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j(jnt)} = 25^{\circ}\text{C}$; (2) $T_{j(jnt)} = 100^{\circ}\text{C}$

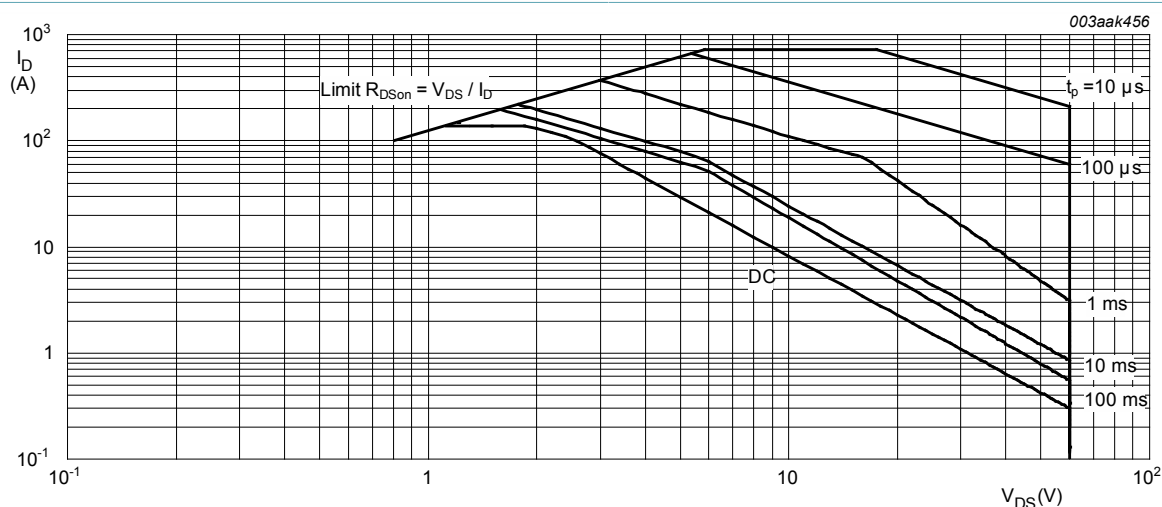


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	0.49	0.57	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

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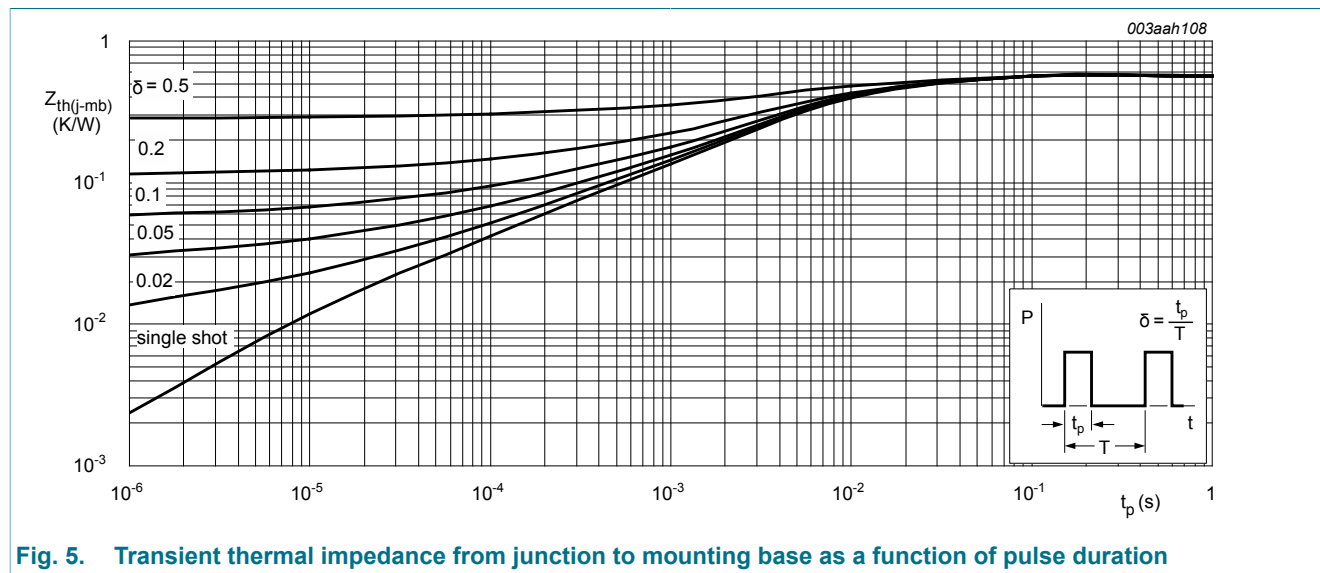


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

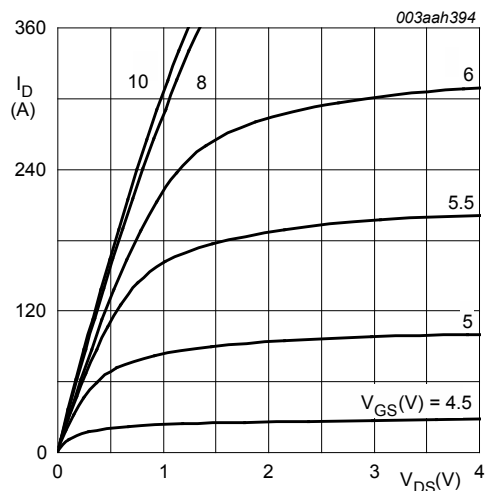
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_J = 25 ^\circ C$	60	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_J = -55 ^\circ C$	54	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 mA; V_{DS} = V_{GS}; T_J = 25 ^\circ C;$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 mA; V_{DS} = V_{GS}; T_J = 175 ^\circ C;$ Fig. 9	1	-	-	V
		$I_D = 1 mA; V_{DS} = V_{GS}; T_J = -55 ^\circ C;$ Fig. 9	-	-	4.5	V
I_{DSS}	drain leakage current	$V_{DS} = 60 V; V_{GS} = 0 V; T_J = 175 ^\circ C$	-	-	500	μA
		$V_{DS} = 60 V; V_{GS} = 0 V; T_J = 25 ^\circ C$	-	0.07	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_J = 25 ^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_J = 25 ^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 25 A; T_J = 25 ^\circ C;$ Fig. 11	-	2.94	3.9	mΩ
		$V_{GS} = 10 V; I_D = 25 A; T_J = 175 ^\circ C;$ Fig. 11; Fig. 12	-	-	8.5	mΩ
R_G	gate resistance	$f = 1 MHz$	0.35	0.7	1.4	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 A; V_{DS} = 48 V; V_{GS} = 10 V;$ Fig. 13; Fig. 14	-	103	-	nC
Q_{GS}	gate-source charge		-	25.1	-	nC

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Q _{GD}	gate-drain charge			-	33	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; Fig. 15		-	5600	-	pF
C _{oss}	output capacitance			-	740	-	pF
C _{rss}	reverse transfer capacitance			-	460	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 45 V; R _L = 1.8 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω		-	25.3	-	ns
t _r	rise time			-	41.4	-	ns
t _{d(off)}	turn-off delay time			-	62.7	-	ns
t _f	fall time			-	45	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 16		-	0.8	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 25 V		-	39	-	ns
Q _r	recovered charge			-	51	-	nC



$T_j = 25\text{ }^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

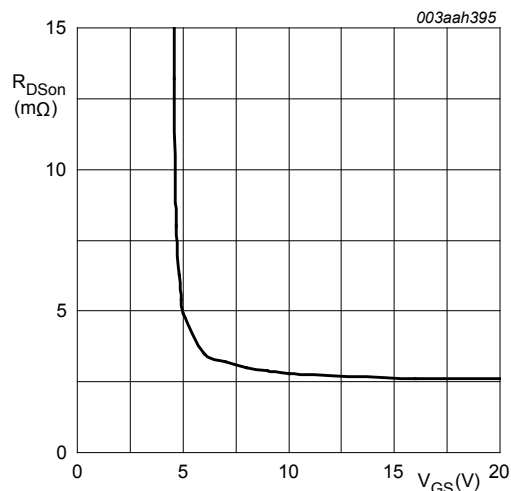


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 25\text{ A}$

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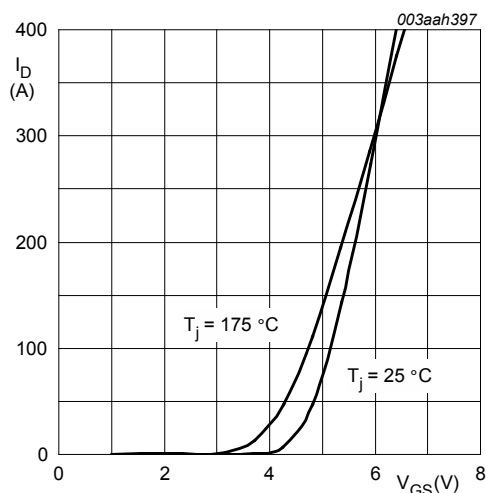


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

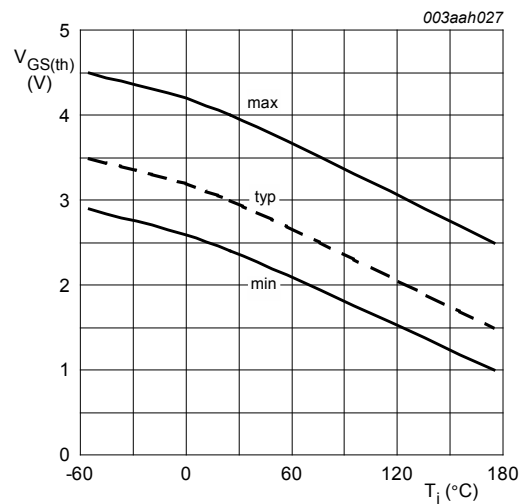


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

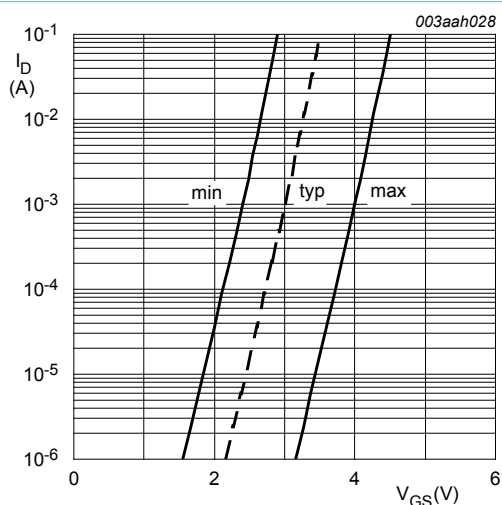
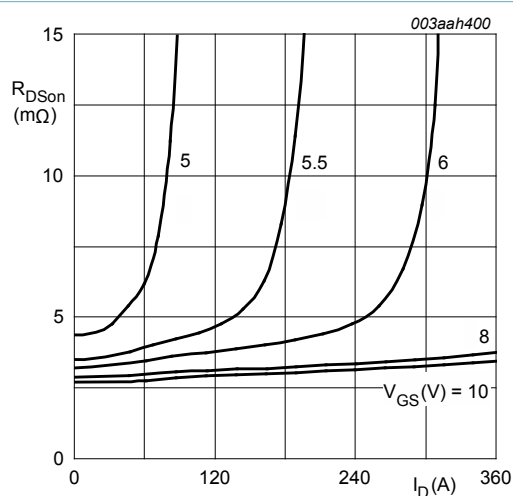


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^\circ\text{C}; V_{DS} = 5V$$



$$T_j = 25^\circ\text{C}; t_p = 300 \mu\text{s}$$

Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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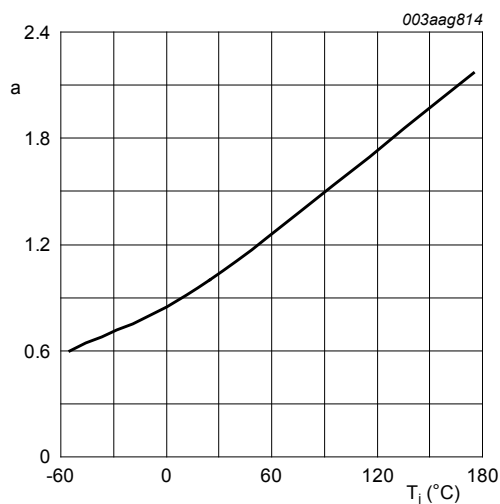


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ\text{C})}}$$

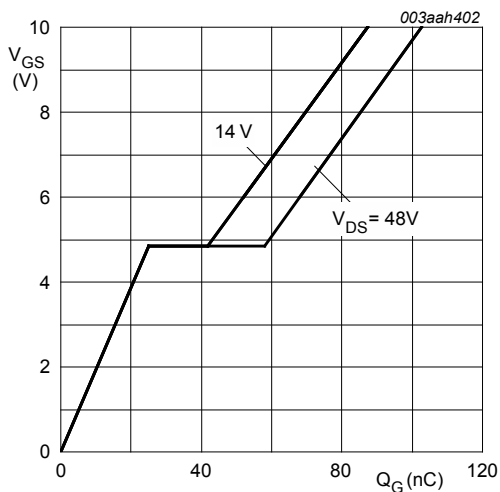


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$

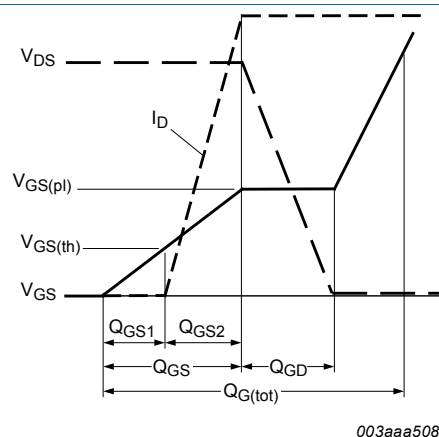


Fig. 13. Gate charge waveform definitions

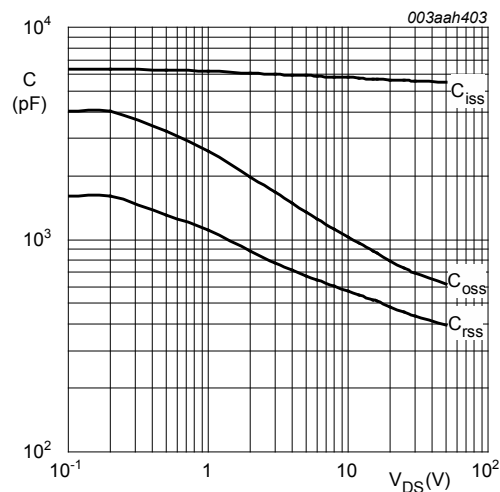


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$

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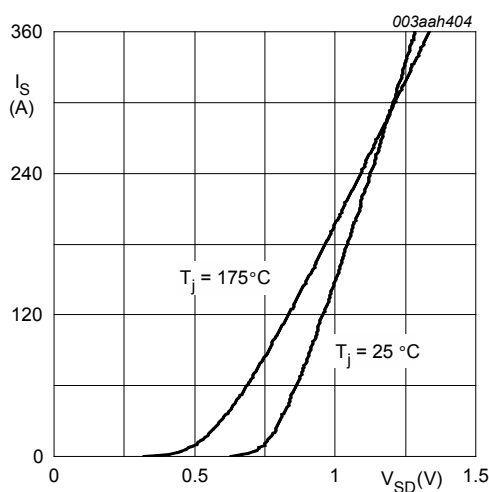


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

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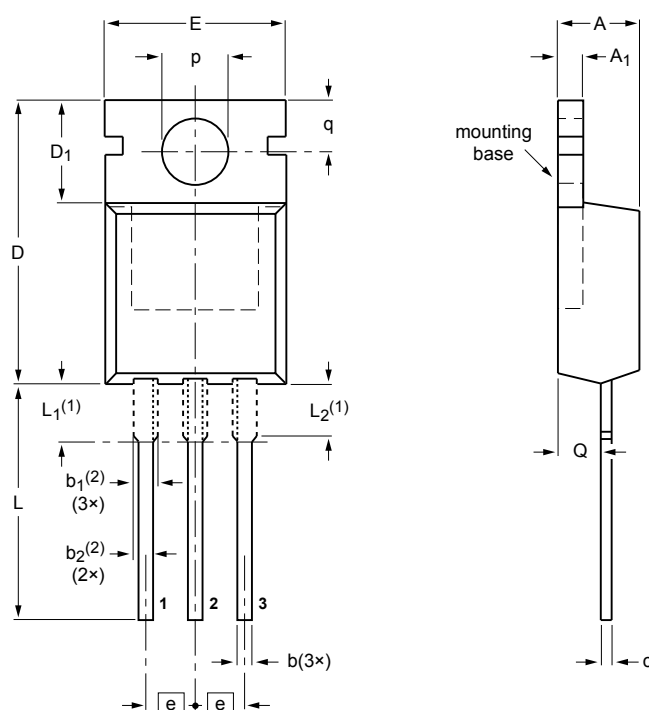
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11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁ (2)	b ₂ (2)	c	D	D ₁	E	e	L	L ₁ (1)	L ₂ (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 17. Package outline TO-220AB (SOT78)

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12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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